

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Patent Application of

T. OSABE et al

Serial No.

Filed: September 4, 2001

For: SEMICONDUCTOR DEVICE

PRELIMINARY AMENDMENT

Commissioner for Patents
Washington, D.C. 20231

Sir:

Prior to examination, please amend the above-identified application as follows.

IN THE CLAIMS

Rewrite claim 10 as follows:

10. (Amended) A semiconductor memory cell in a memory cell array, comprising:

the semiconductor memory cells as defined in claim 5, being aligned in plural numbers thereof, wherein they are driven by a data line and word line, wherein:

drain regions of plural numbers of semiconductor memory cells are connected to a same data line;

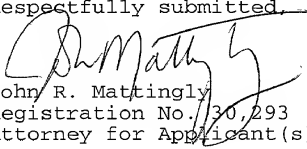
second gates of said plural numbers of said semiconductor memory cells, which are connected to the same data line at said drain regions thereof, are connected with each other; and

first gates of said plural numbers of said semiconductor memory cells, which are connected to the same data line at said drain regions thereof, are connected with word lines, being different from each other.

REMARKS

Examination is requested.

Respectfully submitted


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MARKED UP VERSION OF REWRITTEN CLAIMS

10. (Amended) A semiconductor memory cell in a memory cell array, comprising:

the semiconductor memory cells as defined in [either on of the] claim[s] 5 [to 9], being aligned in plural numbers thereof, wherein they are driven by a data line and word line, wherein:

drain regions of plural numbers of semiconductor memory cells are connected to a same data line;

second gates of said plural numbers of said semiconductor memory cells, which are connected to the same data line at said drain regions thereof, are connected with each other; and

first gates of said plural numbers of said semiconductor memory cells, which are connected to the same data line at said drain regions thereof, are connected with word lines, being different from each other.